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### Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

### Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

#### Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-A9
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Multimedia; NEON™ SIMD
RAM Controllers	LPDDR2, LVDDR3, DDR3
Graphics Acceleration	Yes
Display & Interface Controllers	Keypad, LCD
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 2.0 + PHY (4)
Voltage - I/O	1.8V, 2.5V, 2.8V, 3.3V
Operating Temperature	0°C ~ 95°C (TJ)
Security Features	ARM TZ, Boot Security, Cryptography, RTIC, Secure Fusebox, Secure JTAG, Secure Memory, Secure RTC, Tamper Detection
Package / Case	624-LFBGA
Supplier Device Package	624-MAPBGA (21x21)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx6u5dvm10abr">https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx6u5dvm10abr</a>

## 4.1.7 USB PHY Current Consumption

### 4.1.7.1 Power Down Mode

In power down mode, everything is powered down, including the VBUS valid detectors in typical condition. [Table 14](#) shows the USB interface current consumption in power down mode..

**Table 14. USB PHY Current Consumption in Power Down Mode**

	VDDUSB_CAP (3.0 V)	VDDHIGH_CAP (2.5 V)	NVCC_PLL_OUT (1.1 V)
Current	5.1 $\mu$ A	1.7 $\mu$ A	<0.5 $\mu$ A

#### NOTE

The currents on the VDDHIGH\_CAP and VDDUSB\_CAP were identified to be the voltage divider circuits in the USB-specific level shifters.

## 4.1.8 PCIe 2.0 Power Consumption

[Table 15](#) provides PCIe PHY currents under certain Tx operating modes.

**Table 15. PCIe PHY Current Drain**

Mode	Test Conditions	Supply	Max Current	Unit
PO: Normal Operation	5G Operations	PCIE_VP (1.1 V)	40	mA
		PCIE_VPTX (1.1 V)	20	
		PCIE_VPH (2.5 V)	21	
	2.5G Operations	PCIE_VP (1.1 V)	27	
		PCIE_VPTX (1.1 V)	20	
		PCIE_VPH (2.5 V)	20	
POs: Low Recovery Time Latency, Power Saving State	5G Operations	PCIE_VP (1.1 V)	30	mA
		PCIE_VPTX (1.1 V)	2.4	
		PCIE_VPH (2.5 V)	18	
	2.5G Operations	PCIE_VP (1.1 V)	20	
		PCIE_VPTX (1.1 V)	2.4	
		PCIE_VPH (2.5 V)	18	
P1: Longer Recovery Time Latency, Lower Power State		PCIE_VP (1.1 V)	12	mA
		PCIE_VPTX (1.1 V)	2.4	
		PCIE_VPH (2.5 V)	12	
Power Down		PCIE_VP (1.1 V)	1.3	mA
		PCIE_VPTX (1.1 V)	0.18	
		PCIE_VPH (2.5 V)	0.36	

- VDDARM\_IN supply must be turned ON together with VDDSOC\_IN supply or not delayed more than 1 ms
- VDDARM\_CAP must not exceed VDDSOC\_CAP by more than 50 mV.

### NOTE

The POR\_B input (if used) must be immediately asserted at power-up and remain asserted until after the last power rail reaches its working voltage. In the absence of an external reset feeding the POR\_B input, the internal POR module takes control. See the *i.MX 6Solo/6DualLite Reference Manual* for further details and to ensure that all necessary requirements are being met.

### NOTE

Need to ensure that there is no back voltage (leakage) from any supply on the board towards the 3.3 V supply (for example, from the external components that use both the 1.8 V and 3.3 V supplies).

### NOTE

USB\_OTG\_VBUS and USB\_H1\_VBUS are not part of the power supply sequence and may be powered at any time.

## 4.2.2 Power-Down Sequence

No special restrictions for i.MX 6Solo/6DualLite IC.

## 4.2.3 Power Supplies Usage

All I/O pins should not be externally driven while the I/O power supply for the pin (NVCC\_XXX) is OFF. This can cause internal latch-up and malfunctions due to reverse current flows. For information about I/O power supply of each pin, see “Power Rail” columns in pin list tables of [Section 6, “Package Information and Contact Assignments.”](#)

## 4.3 Integrated LDO Voltage Regulator Parameters

Various internal supplies can be powered ON from internal LDO voltage regulators. All the supply pins named \*\_CAP must be connected to external capacitors. The onboard LDOs are intended for internal use only and should not be used to power any external circuitry. See the *i.MX 6Solo/6DualLite Reference Manual (IMX6SDLRM)* for details on the power tree scheme.

### NOTE

The \*\_CAP signals should not be powered externally. These signals are intended for internal LDO or LDO bypass operation only.

### 4.3.1 Digital Regulators (LDO\_ARM, LDO\_PU, LDO\_SOC)

There are three digital LDO regulators (“Digital”, because of the logic loads that they drive, not because of their construction). The advantages of the regulators are to reduce the input supply variation because of

Table 23. GPIO DC Parameters (continued)

Low-Level input voltage <sup>1,2</sup>	VIL		0	0.3*OVDD D	V
Input Hysteresis(OVDD= 1.8V)	VHYS_LowVDD	OVDD=1.8V	250		mV
Input Hysteresis(OVDD=3.3V)	VHYS_HighVDD	OVDD=3.3V	250		mV
Schmitt trigger VT+ <sup>2,3</sup>	VTH+		0.5*OVDD D		mV
Schmitt trigger VT- <sup>2,3</sup>	VTH-			0.5*OVDD D	mV
Pull-up resistor (22_kΩ PU)	RPU_22K	Vin=0V		212	μA
Pull-up resistor (22_kΩ PU)	RPU_22K	Vin=OVDD		1	μA
Pull-up resistor (47_kΩ PU)	RPU_47K	Vin=0V		100	μA
Pull-up resistor (47_kΩ PU)	RPU_47K	Vin=OVDD		1	μA
Pull-up resistor (100_kΩ PU)	RPU_100K	Vin=0V		48	μA
Pull-up resistor (100_kΩ PU)	RPU_100K	Vin=OVDD		1	μA
Pull-down resistor (100_kΩ PD)	RPD_100K	Vin=OVDD		48	μA
Pull-down resistor (100_kΩ PD)	RPD_100K	Vin=0V		1	μA
Input current (no PU/PD)	IIN	VI = 0, VI = OVDD	-1	1	μA
Keeper Circuit Resistance	R_Keeper	VI = .3*OVDD, VI = .7* OVDD	105	175	kΩ

<sup>1</sup> Overshoot and undershoot conditions (transitions above OVDD and below GND) on switching pads must be held below 0.6 V, and the duration of the overshoot/undershoot must not exceed 10% of the system clock cycle. Overshoot/undershoot must be controlled through printed circuit board layout, transmission line impedance matching, signal line termination, or other methods. Non-compliance to this specification may affect device reliability or cause permanent damage to the device.

<sup>2</sup> To maintain a valid level, the transition edge of the input must sustain a constant slew rate (monotonic) from the current DC level through to the target DC level, Vil or Vih. Monotonic input transition time is from 0.1 ns to 1 s.

<sup>3</sup> Hysteresis of 250 mV is guaranteed over all operating conditions when hysteresis is enabled.

## 4.6.2 DDR I/O DC Parameters

The DDR I/O pads support LPDDR2 and DDR3/DDR3L operational modes.

### 4.6.2.1 LPDDR2 Mode I/O DC Parameters

The LPDDR2 interface mode fully complies with JESD209-2B LPDDR2 JEDEC standard release June, 2009.

Table 24. LPDDR2 I/O DC Electrical Parameters<sup>1</sup>

Parameters	Symbol	Test Conditions	Min	Max	Unit
High-level output voltage	VOH	Ioh= -0.1mA	0.9*OVDD		V
Low-level output voltage	VOL	Iol= 0.1mA		0.1*OVDD	V
Input Reference Voltage	Vref		0.49*OVDD	0.51*OVDD	V

### 4.9.3.3 General EIM Timing-Synchronous Mode

Figure 10, Figure 11, and Table 39 specify the timings related to the EIM module. All EIM output control signals may be asserted and deasserted by an internal clock synchronized to the BCLK rising edge according to corresponding assertion/negation control fields.

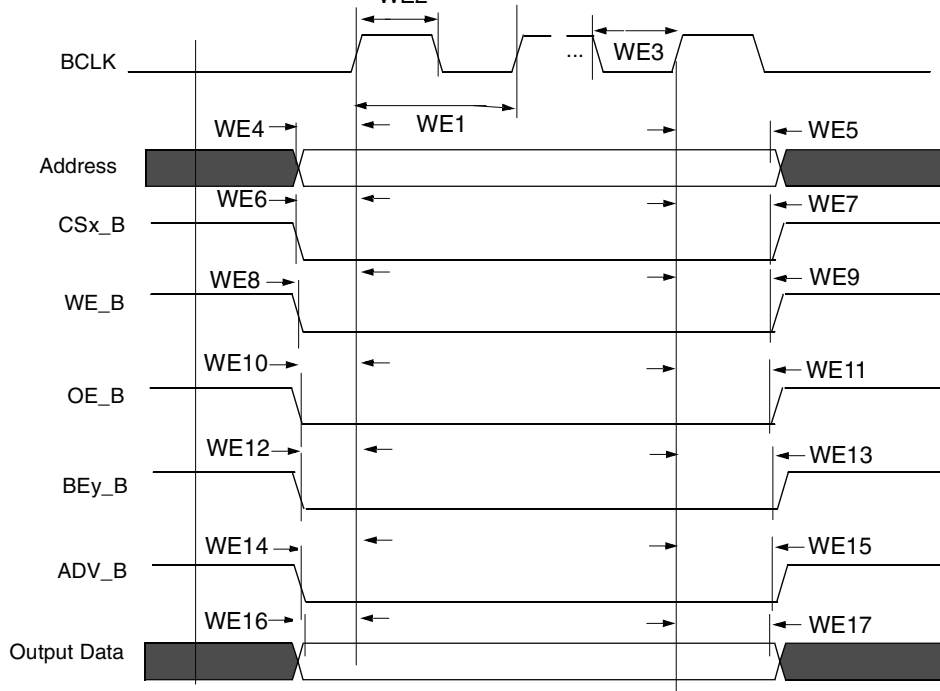


Figure 10. EIM Outputs Timing Diagram

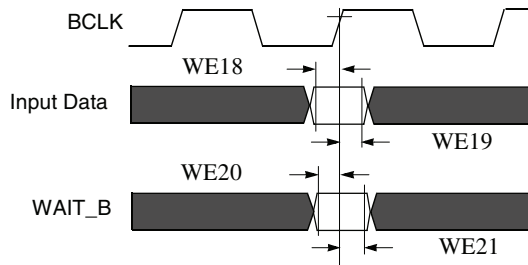


Figure 11. EIM Inputs Timing Diagram

Table 39. EIM Bus Timing Parameters (continued)<sup>1</sup>

ID	Parameter	BCD = 0		BCD = 1		BCD = 2		BCD = 3	
		Min	Max	Min	Max	Min	Max	Min	Max
WE19	Input Data hold time from Clock rise	2	—	2	—	—	—	—	—
WE20	WAIT_B setup time to Clock rise	2	—	4	—	—	—	—	—
WE21	WAIT_B hold time from Clock rise	2	—	2	—	—	—	—	—

<sup>1</sup> t is the maximal EIM logic (axi\_clk) cycle time. The maximum allowed axi\_clk frequency depends on the fixed/non-fixed latency configuration, whereas the maximum allowed BCLK frequency is:

- Fixed latency for both read and write is 132 MHz.
- Variable latency for read only is 132 MHz.
- Variable latency for write only is 52 MHz.

In variable latency configuration for write, if BCD = 0 & WBCDD = 1 or BCD = 1, axi\_clk must be 104 MHz. Write BCD = 1 and 104 MHz axi\_clk, will result in a BCLK of 52 MHz. When the clock branch to EIM is decreased to 104 MHz, other buses are impacted which are clocked from this source. See the CCM chapter of the *i.MX 6Solo/6DualLite Reference Manual (IMX6SDLRM)* for a detailed clock tree description.

<sup>2</sup> BCLK parameters are being measured from the 50% point, that is, high is defined as 50% of signal value and low is defined as 50% as signal value.

<sup>3</sup> For signal measurements, “High” is defined as 80% of signal value and “Low” is defined as 20% of signal value.

Figure 12 to Figure 15 provide few examples of basic EIM accesses to external memory devices with the timing parameters mentioned previously for specific control parameters settings.

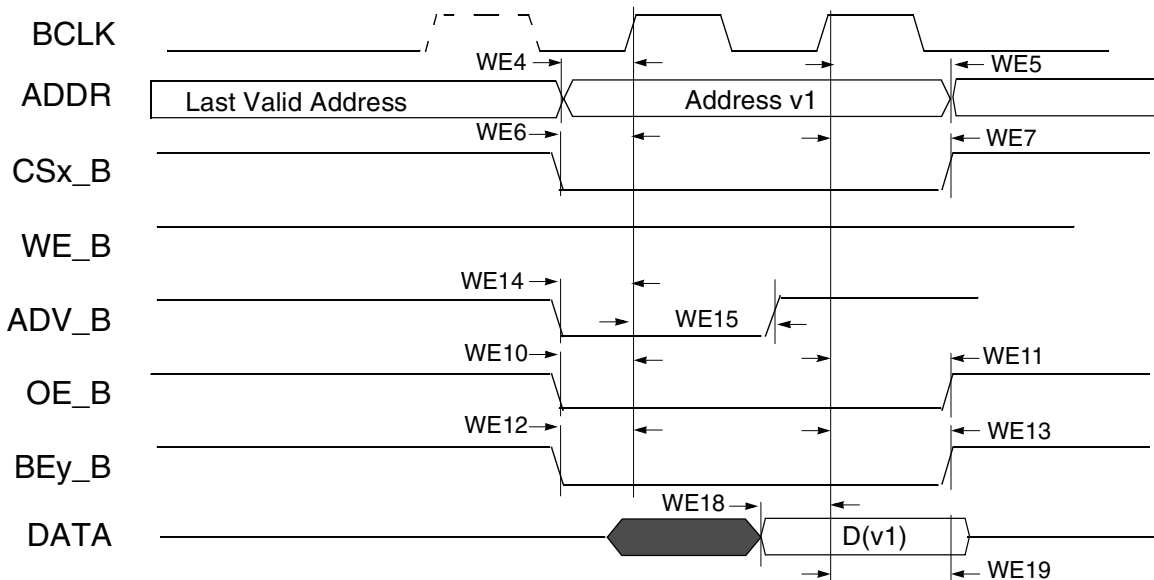


Figure 12. Synchronous Memory Read Access, WSC=1

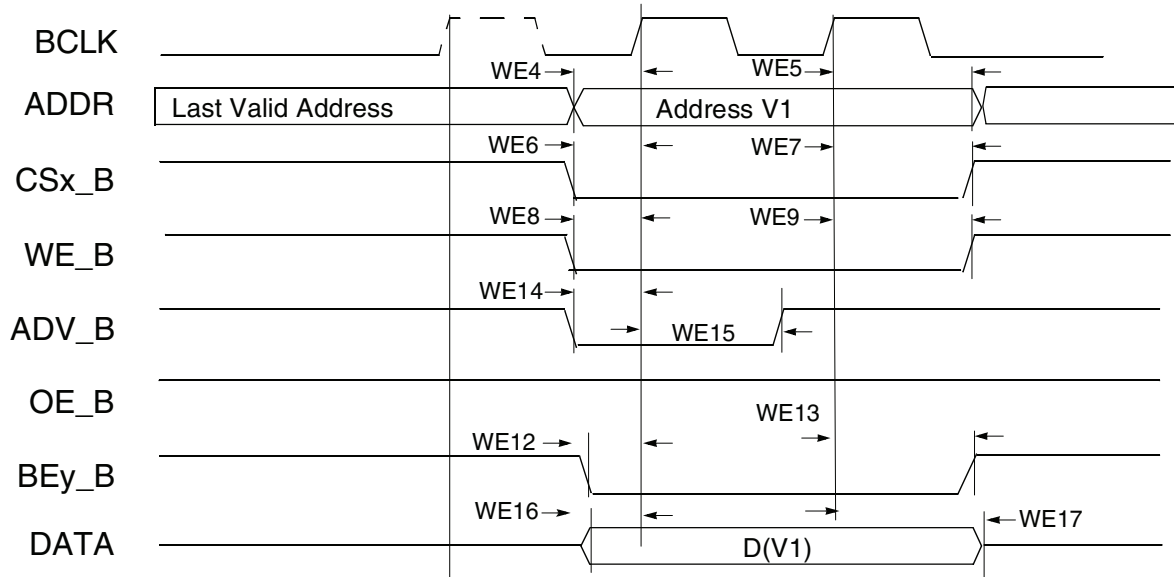


Figure 13. Synchronous Memory, Write Access, WSC=1, WBEA=0 and WADVN=0

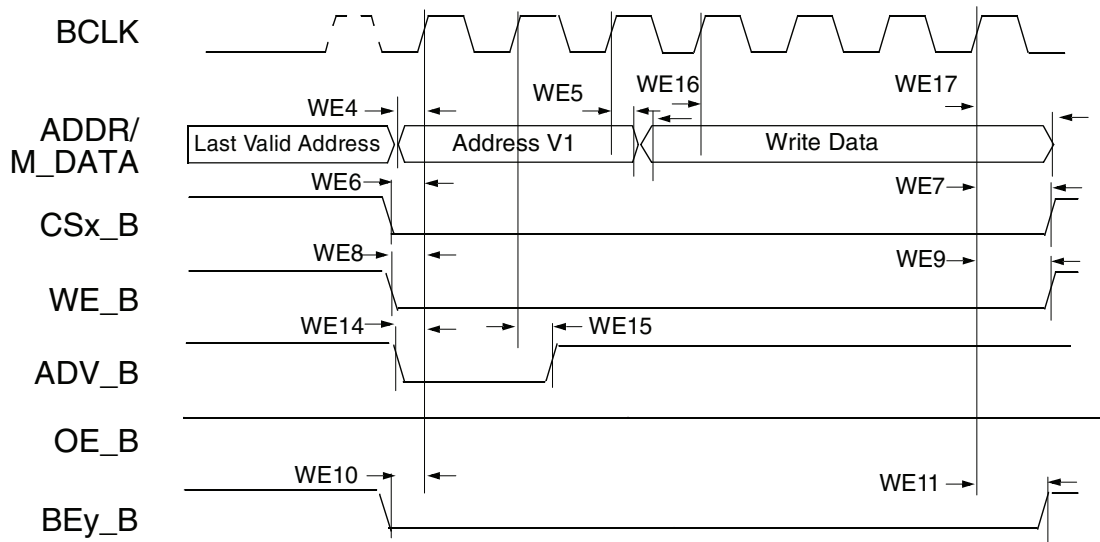


Figure 14. Muxed Address/Data (A/D) Mode, Synchronous Write Access, WSC=6, ADVA=0, ADVN=1, and ADH=1

**NOTE**

In 32-bit muxed address/data (A/D) mode the 16 MSBs are driven on the data bus.

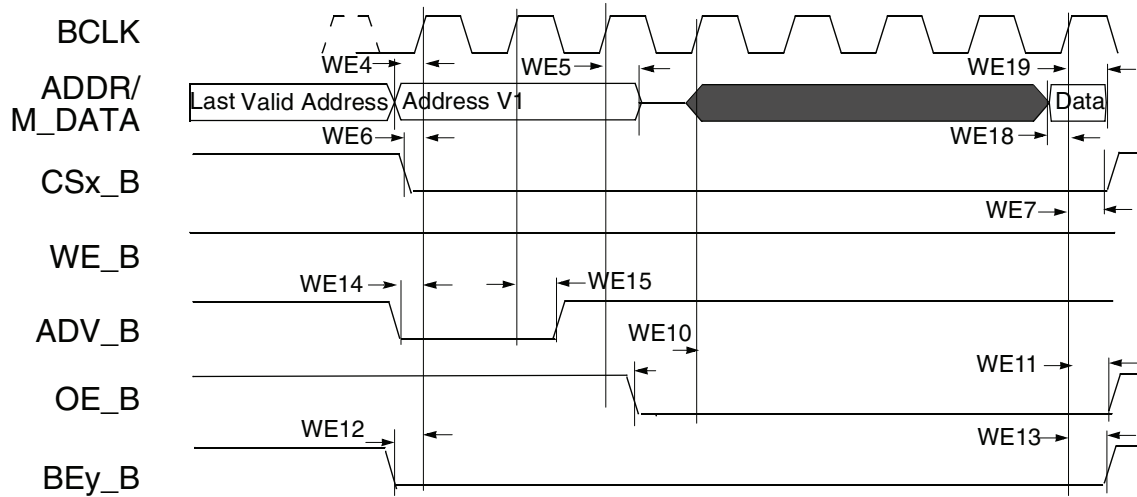


Figure 15. 16-Bit Muxed A/D Mode, Synchronous Read Access, WSC=7, RADVN=1, ADH=1, OEA=0

### 4.9.3.5 General EIM Timing-Asynchronous Mode

Figure 16 through Figure 20, and Table 40 help you determine timing parameters relative to the chip select (CS) state for asynchronous and DTACK EIM accesses with corresponding EIM bit fields and the timing parameters mentioned above.

Asynchronous read & write access length in cycles may vary from what is shown in Figure 16 through Figure 19 as RWSC, OEN & CSN is configured differently. See the *i.MX 6Solo/6DualLite Reference Manual (IMX6SDLRM)* for the EIM programming model.



### 4.9.4 DDR SDRAM Specific Parameters (DDR3/DDR3L and LPDDR2)

#### 4.9.4.1 DDR3/DDR3L Parameters

Figure 22 shows the basic timing parameters. The timing parameters for this diagram appear in Table 41.

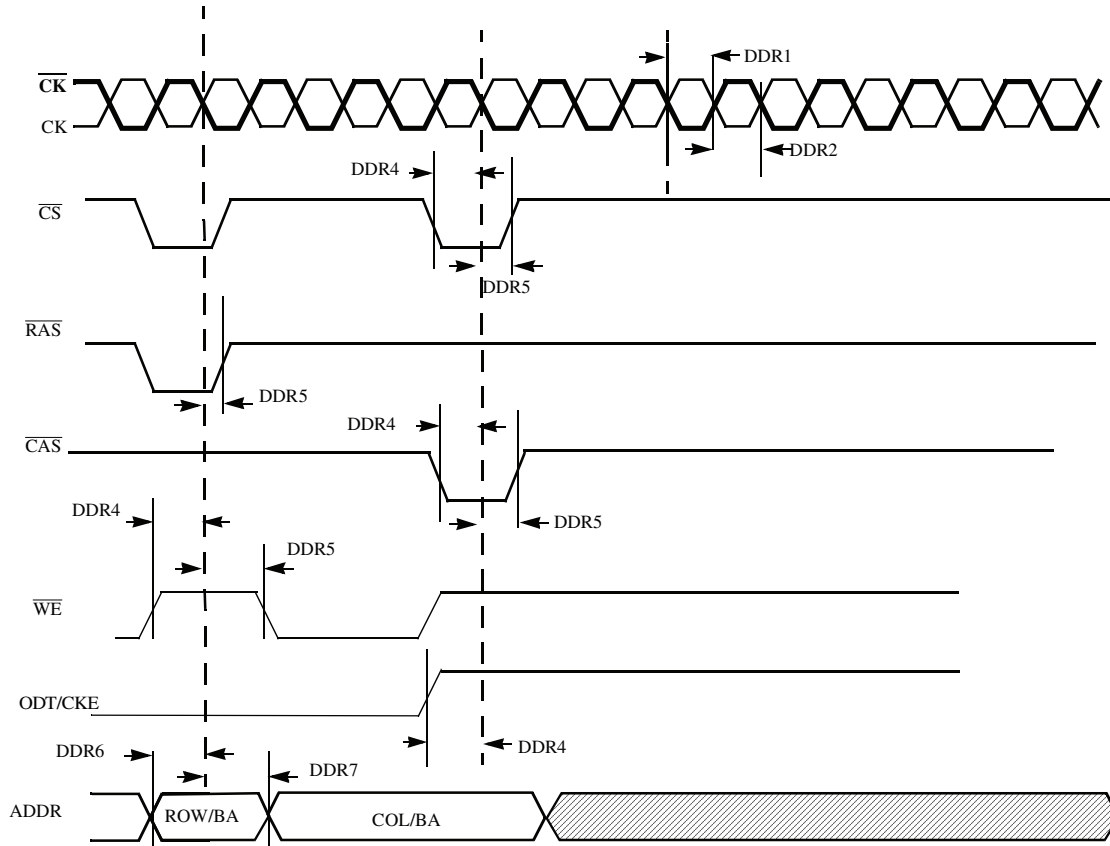


Figure 22. DDR3 Command and Address Timing Parameters

Table 41. DDR3/DDR3L Timing Parameter Table

ID	Parameter	Symbol	CK = 400 MHz		Unit
			Min	Max	
DDR1	CK clock high-level width	t <sub>CH</sub>	0.47	0.53	t <sub>CK</sub>
DDR2	CK clock low-level width	t <sub>CL</sub>	0.47	0.53	t <sub>CK</sub>
DDR4	CS, RAS, CAS, CKE, WE, ODT setup time	t <sub>IS</sub>	800	—	ps
DDR5	CS, RAS, CAS, CKE, WE, ODT hold time	t <sub>IH</sub>	580	—	ps
DDR6	Address output setup time	t <sub>IS</sub>	800	—	ps
DDR7	Address output hold time	t <sub>IH</sub>	580	—	ps

Table 47. Asynchronous Mode Timing Parameters<sup>1</sup> (continued)

ID	Parameter	Symbol	Timing T = GPMI Clock Cycle		Example Timing for GPMI Clock ≈ 100 MHz T = 10 ns		Unit
			Min.	Max.	Min.	Max.	
NF5	$\overline{WE}$ pulse width	tWP	DS x T		10		ns
NF6	ALE setup time	tALS	(AS+1) x T	—	10	—	ns
NF7	ALE hold time	tALH	(DH+1) x T	—	20	—	ns
NF8	Data setup time	tDS	DS x T	—	10	—	ns
NF9	Data hold time	tDH	DH x T	—	10	—	ns
NF10	Write cycle time	tWC	(DS+DH) x T		20		ns
NF11	$\overline{WE}$ hold time	tWH	DH x T		10		ns
NF12	Ready to $\overline{RE}$ low	tRR	(AS+1) x T	—	10	—	ns
NF13	$\overline{RE}$ pulse width	tRP	DS x T	—	10	—	ns
NF14	READ cycle time	tRC	(DS+DH) x T	—	20	—	ns
NF15	$\overline{RE}$ high hold time	tREH	DH x T		10	—	ns
NF16	Data setup on read	tDSR	N/A		10	—	ns
NF17	Data hold on read	tDHR	N/A		10	—	ns

<sup>1</sup> GPMI's Async Mode output timing could be controlled by module's internal registers, say HW\_GPMI\_TIMING0\_ADDRESS\_SETUP, HW\_GPMI\_TIMING0\_DATA\_SETUP, and HW\_GPMI\_TIMING0\_DATA\_HOLD. This AC timing depends on these registers' settings. In the above table, we use AS/DS/DH to represent each of these settings.

2) AS minimum value could be 0, while DS/DH minimum value is 1.

3) T represents for the GPMI clock period.

In EDO mode (Figure 31), NF16/NF17 are different from the definition in non-EDO mode (Figure 30). They are called tREA/tRHOH (RE# access time/RE# HIGH to output hold). The typical value for them are 16 ns (max for tREA)/15 ns (min for tRHOH) at 50 MB/s EDO mode. In EDO mode, GPMI will sample IO[7:0] at rising edge of delayed RE provided by an internal DPLL. The delay value can be controlled by GPMI\_CTRL1.RDN\_DELAY (see the GPMI chapter of the i.MX 6Solo/6DualLite reference manual). The typical value of this control register is 0x8 at 50 MT/s EDO mode. But if the board delay is big enough and cannot be ignored, the delay value should be made larger to compensate the board delay.

### 4.10.2 Source Synchronous Mode AC Timing (ONFI 2.x Compatible)

Figure 32 to Figure 34 show the write and read timing of Source Synchronous Mode.

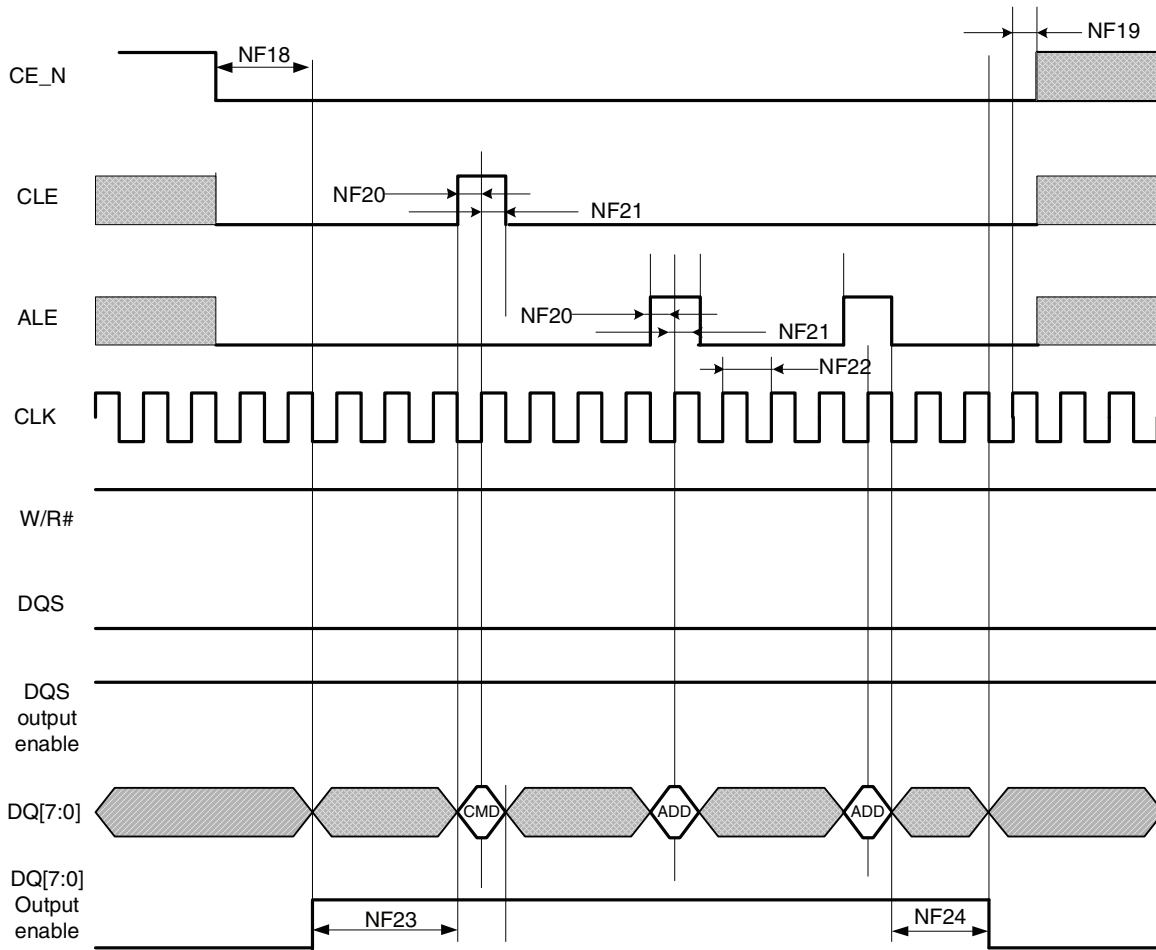


Figure 32. Source Synchronous Mode Command and Address Timing Diagram

Table 49. Samsung Toggle Mode Timing Parameters (continued)

ID	Parameter	Symbol	Timing T = GPMI Clock Cycle		Unit
			Min.	Max.	
NF23	preamble delay	tPRE	(PRE_DELAY+1) x tCK	—	ns
NF24	postamble delay	tPOST	POST_DELAY x tCK	—	ns
NF25	CLE and ALE setup time	tCALS	0.5 x tCK	—	ns
NF26	CLE and ALE hold time	tCALH	0.5 x tCK	—	ns

For DDR Toggle mode, [Figure 35](#) shows the timing diagram of DQS/DQ read valid window. The typical value of tDQSQ is 1.4 ns(max) and 1.4 ns (max) for tQHS at 133 MB/s. GPMI will sample DQ[7:0] at both rising and falling edge of an delayed DQS signal, which is provided by an internal DPLL. The delay value of this register can be controlled by GPMI register

GPMI\_READ\_DDR\_DLL\_CTRL.SLV\_DLY\_TARGET (see the GPMI chapter of the i.MX 6Solo/6DualLite reference manual). Generally, the typical delay value is equal to 0x7 which means 1/4 clock cycle delay expected. But if the board delay is big enough and cannot be ignored, the delay value should be made larger to compensate the board delay.

## 4.11 External Peripheral Interface Parameters

The following subsections provide information on external peripheral interfaces.

### 4.11.1 AUDMUX Timing Parameters

The AUDMUX provides a programmable interconnect logic for voice, audio, and data routing between internal serial interfaces (SSIs) and external serial interfaces (audio and voice codecs). The AC timing of AUDMUX external pins is governed by the SSI module. For more information, see the respective SSI electrical specifications found within this document.

### 4.11.2 ECSPI Timing Parameters

This section describes the timing parameters of the ECSPI blocks. The ECSPI have separate timing parameters for master and slave modes.

Table 54. eMMC4.4 Interface Timing Specification (continued)

ID	Parameter	Symbols	Min	Max	Unit
<b>uSDHC Input / Card Outputs CMD, DAT (Reference to CLK)</b>					
SD3	uSDHC Input Setup Time	$t_{ISU}$	2.6	—	ns
SD4	uSDHC Input Hold Time	$t_{IH}$	1.5	—	ns

### 4.11.4.3 SDR50/SDR104 AC Timing

Figure 44 depicts the timing of SDR50/SDR104, and Table 55 lists the SDR50/SDR104 timing characteristics.

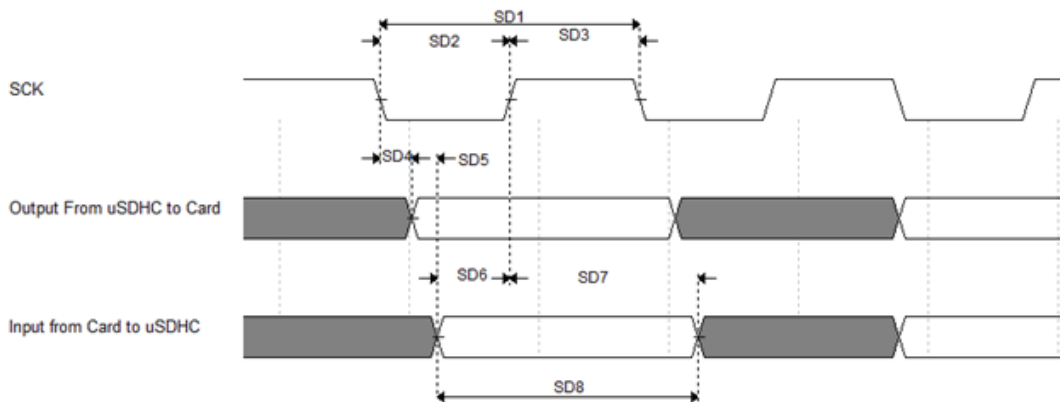


Figure 44. SDR50/SDR104 Timing

Table 55. SDR50/SDR104 Interface Timing Specification

ID	Parameter	Symbols	Min	Max	Unit
<b>Card Input Clock</b>					
SD1	Clock Frequency Period	$t_{CLK}$	4.8	—	ns
SD2	Clock Low Time	$t_{CL}$	$0.3*t_{CLK}$	$0.7*t_{CLK}$	ns
SD2	Clock High Time	$t_{CH}$	$0.3*t_{CLK}$	$0.7*t_{CLK}$	ns
<b>uSDHC Output/Card Inputs CMD, DAT in SDR50 (Reference to CLK)</b>					
SD4	uSDHC Output Delay	$t_{OD}$	-3	1	ns
<b>uSDHC Output/Card Inputs CMD, DAT in SDR104 (Reference to CLK)</b>					
SD5	uSDHC Output Delay	$t_{OD}$	-1.6	1	ns
<b>uSDHC Input/Card Outputs CMD, DAT in SDR50 (Reference to CLK)</b>					
SD6	uSDHC Input Setup Time	$t_{ISU}$	2.5	—	ns

Table 55. SDR50/SDR104 Interface Timing Specification (continued)

ID	Parameter	Symbols	Min	Max	Unit
SD7	uSDHC Input Hold Time	$t_{IH}$	1.5	—	ns
<b>uSDHC Input/Card Outputs CMD, DAT in SDR104 (Reference to CLK)<sup>1</sup></b>					
SD8	Card Output Data Window	$t_{ODW}$	$0.5 \cdot t_{CLK}$	—	ns

<sup>1</sup>Data window in SDR100 mode is variable.

#### 4.11.4.4 Bus Operation Condition for 3.3 V and 1.8 V Signaling

Signaling level of SD/eMMC4.3 and eMMC4.4 modes is 3.3 V. Signaling level of SDR104/SDR50 mode is 1.8 V. The DC parameters for the NVCC\_SD1, NVCC\_SD2 and NVCC\_SD3 supplies are identical to those shown in Table 23, "GPIO DC Parameters," on page 37.

#### 4.11.5 Ethernet Controller (ENET) AC Electrical Specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

##### 4.11.5.1 ENET MII Mode Timing

This subsection describes MII receive, transmit, asynchronous inputs, and serial management signal timings.

##### 4.11.5.1.1 MII Receive Signal Timing (ENET\_RX\_DATA3,2,1,0, ENET\_RX\_EN, ENET\_RX\_ER, and ENET\_RX\_CLK)

The receiver functions correctly up to an ENET\_RX\_CLK maximum frequency of 25 MHz + 1%. There is no minimum frequency requirement. Additionally, the processor clock frequency must exceed twice the ENET\_RX\_CLK frequency.

Table 64. I<sup>2</sup>C Module Timing Parameters (continued)

ID	Parameter	Standard Mode		Fast Mode		Unit
		Min	Max	Min	Max	
IC8	Data set-up time	250	—	100 <sup>3</sup>	—	ns
IC9	Bus free time between a STOP and START condition	4.7	—	1.3	—	μs
IC10	Rise time of both I2DAT and I2CLK signals	—	1000	$20 + 0.1C_b^4$	300	ns
IC11	Fall time of both I2DAT and I2CLK signals	—	300	$20 + 0.1C_b^4$	300	ns
IC12	Capacitive load for each bus line ( $C_b$ )	—	400	—	400	pF

<sup>1</sup> A device must internally provide a hold time of at least 300 ns for I2DAT signal in order to bridge the undefined region of the falling edge of I2CLK.

<sup>2</sup> The maximum hold time has only to be met if the device does not stretch the LOW period (ID no IC5) of the I2CLK signal.

<sup>3</sup> A Fast-mode I<sup>2</sup>C-bus device can be used in a Standard-mode I<sup>2</sup>C-bus system, but the requirement of Set-up time (ID No IC7) of 250 ns must be met. This automatically is the case if the device does not stretch the LOW period of the I2CLK signal. If such a device does stretch the LOW period of the I2CLK signal, it must output the next data bit to the I2DAT line  $\text{max\_rise\_time (IC9)} + \text{data\_setup\_time (IC7)} = 1000 + 250 = 1250$  ns (according to the Standard-mode I<sup>2</sup>C-bus specification) before the I2CLK line is released.

<sup>4</sup>  $C_b$  = total capacitance of one bus line in pF.

#### 4.11.10 Image Processing Unit (IPU) Module Parameters

The purpose of the IPU is to provide comprehensive support for the flow of data from an image sensor and/or to a display device. This support covers all aspects of these activities:

- Connectivity to relevant devices—cameras, displays, graphics accelerators, and TV encoders.
- Related image processing and manipulation: sensor image signal processing, display processing, image conversions, and other related functions.
- Synchronization and control capabilities, such as avoidance of tearing artifacts.

Table 67. Video Signal Cross-Reference

i.MX 6Solo/6DualLite	LCD							Comment <sup>1</sup>
Port Name (x=0, 1)	RGB, Signal Name (General)	RGB/TV Signal Allocation (Example)						
		16-bit RGB	18-bit RGB	24 Bit RGB	8-bit Y/Cb <sup>2</sup>	16-bit Y/Cb	20-bit Y/Cb	
DISPx_DAT0	DAT[0]	B[0]	B[0]	B[0]	Y/C[0]	C[0]	C[0]	The restrictions are as follows: <ul style="list-style-type: none"> <li>• There are maximal three continuous groups of bits that could be independently mapped to the external bus. Groups should not be overlapped.</li> <li>• The bit order is expressed in each of the bit groups, for example, B[0] = least significant blue pixel bit</li> </ul>
DISPx_DAT1	DAT[1]	B[1]	B[1]	B[1]	Y/C[1]	C[1]	C[1]	
DISPx_DAT2	DAT[2]	B[2]	B[2]	B[2]	Y/C[2]	C[2]	C[2]	
DISPx_DAT3	DAT[3]	B[3]	B[3]	B[3]	Y/C[3]	C[3]	C[3]	
DISPx_DAT4	DAT[4]	B[4]	B[4]	B[4]	Y/C[4]	C[4]	C[4]	
DISPx_DAT5	DAT[5]	G[0]	B[5]	B[5]	Y/C[5]	C[5]	C[5]	
DISPx_DAT6	DAT[6]	G[1]	G[0]	B[6]	Y/C[6]	C[6]	C[6]	
DISPx_DAT7	DAT[7]	G[2]	G[1]	B[7]	Y/C[7]	C[7]	C[7]	
DISPx_DAT8	DAT[8]	G[3]	G[2]	G[0]	—	Y[0]	C[8]	
DISPx_DAT9	DAT[9]	G[4]	G[3]	G[1]	—	Y[1]	C[9]	
DISPx_DAT10	DAT[10]	G[5]	G[4]	G[2]	—	Y[2]	Y[0]	
DISPx_DAT11	DAT[11]	R[0]	G[5]	G[3]	—	Y[3]	Y[1]	
DISPx_DAT12	DAT[12]	R[1]	R[0]	G[4]	—	Y[4]	Y[2]	
DISPx_DAT13	DAT[13]	R[2]	R[1]	G[5]	—	Y[5]	Y[3]	
DISPx_DAT14	DAT[14]	R[3]	R[2]	G[6]	—	Y[6]	Y[4]	
DISPx_DAT15	DAT[15]	R[4]	R[3]	G[7]	—	Y[7]	Y[5]	
DISPx_DAT16	DAT[16]	—	R[4]	R[0]	—	—	Y[6]	
DISPx_DAT17	DAT[17]	—	R[5]	R[1]	—	—	Y[7]	
DISPx_DAT18	DAT[18]	—	—	R[2]	—	—	Y[8]	
DISPx_DAT19	DAT[19]	—	—	R[3]	—	—	Y[9]	
DISPx_DAT20	DAT[20]	—	—	R[4]	—	—	—	
DISPx_DAT21	DAT[21]	—	—	R[5]	—	—	—	



**Table 71. Electrical and Timing Information (continued)**

$V_{IDTL}$	Differential input low voltage threshold		-70			mV
$V_{IHHS}$	Single ended input high voltage				460	mV
$V_{ILHS}$	Single ended input low voltage		-40			mV
$V_{CMRXDC}$	Input common mode voltage		70		330	mV
$Z_{ID}$	Differential input impedance		80		125	$\Omega$
LP Line Receiver DC Specifications						
$V_{IL}$	Input low voltage				550	mV
$V_{IH}$	Input high voltage		920			mV
$V_{HYST}$	Input hysteresis		25			mV
Contention Line Receiver DC Specifications						
$V_{ILF}$	Input low fault threshold		200		450	mV

### 4.11.13 HSI Host Controller Timing Parameters

This section describes the timing parameters of the HSI Host Controller which are compliant with High-speed Synchronous Serial Interface (HSI) Physical Layer specification version 1.01.

#### 4.11.13.1 Synchronous Data Flow

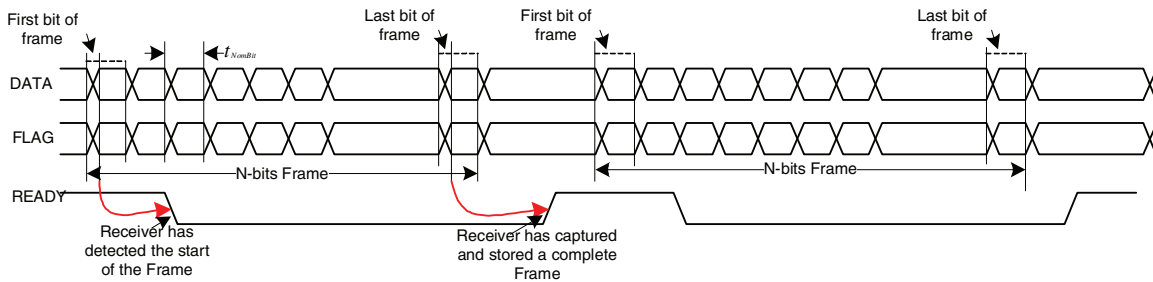


Figure 76. Synchronized Data Flow READY Signal Timing (Frame and Stream Transmission)

#### 4.11.13.2 Pipelined Data Flow

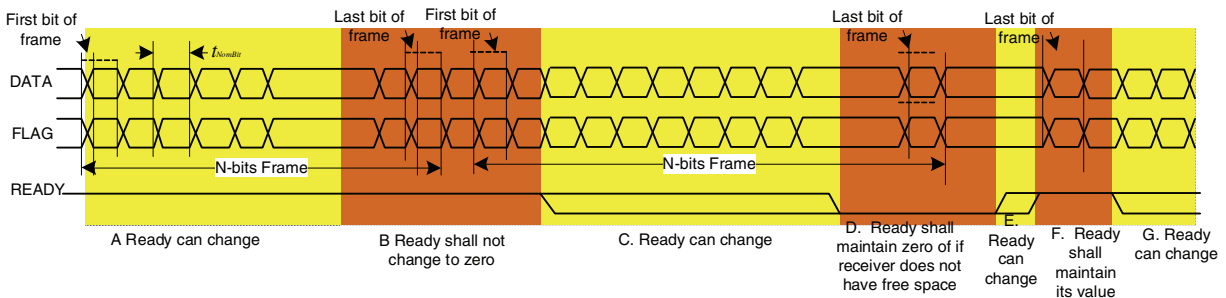


Figure 77. Pipelined Data Flow Ready Signal Timing (Frame Transmission Mode)

#### 4.11.13.3 Receiver Real-Time Data Flow

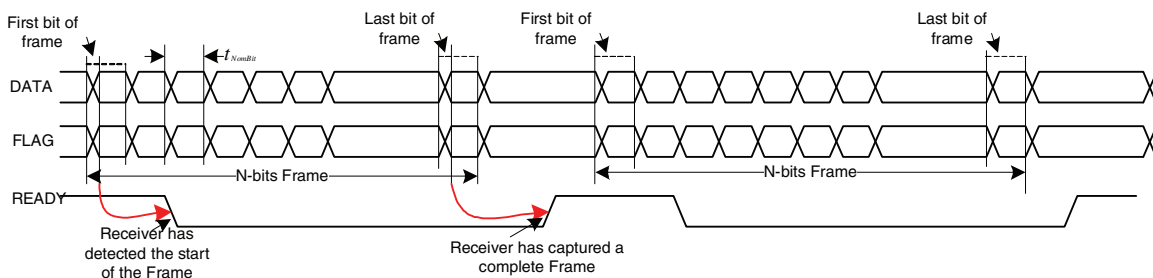


Figure 78. Receiver Real-Time Data Flow READY Signal Timing

### 4.11.14 PCIe PHY Parameters

The PCIe interface complies with PCIe specification Gen2 x1 lane and supports the PCI Express 1.1/2.0 standard.

#### 4.11.14.1 PCIE\_REXT Reference Resistor Connection

The impedance calibration process requires connection of reference resistor 200 Ω, 1% precision resistor on PCIE\_REXT pads to ground. It is used for termination impedance calibration.

### 4.11.15 Pulse Width Modulator (PWM) Timing Parameters

This section describes the electrical information of the PWM. The PWM can be programmed to select one of three clock signals as its source frequency. The selected clock signal is passed through a prescaler before being input to the counter. The output is available at the pulse-width modulator output (PWMO) external pin.

Figure 84 depicts the timing of the PWM, and Table 74 lists the PWM timing parameters.

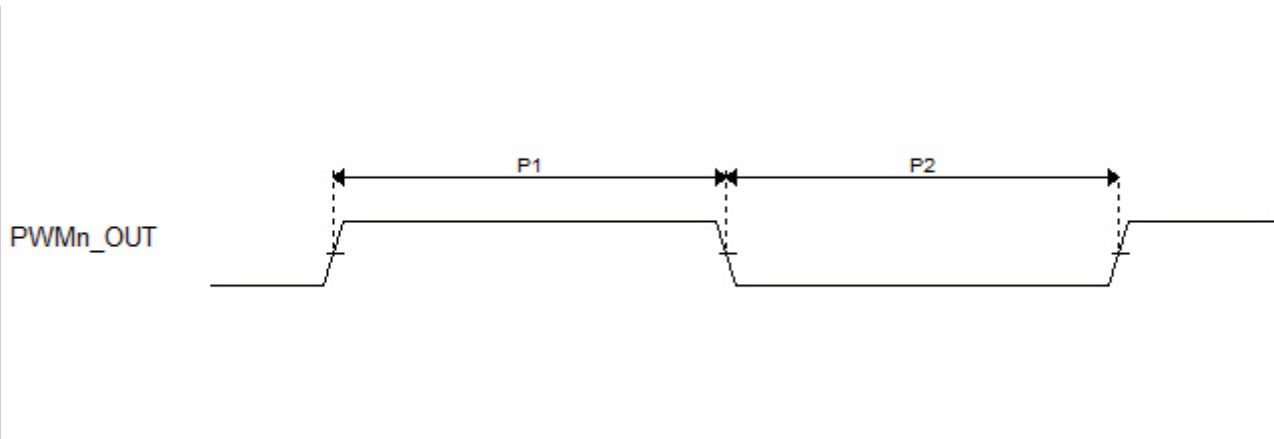


Figure 84. PWM Timing

Table 74. PWM Output Timing Parameters

ID	Parameter	Min	Max	Unit
	PWM Module Clock Frequency	0	ipg_clk	MHz
P1	PWM output pulse width high	15		ns
P2	PWM output pulse width low	15		ns

#### 4.11.18.4 SSI Receiver Timing with External Clock

Figure 94 depicts the SSI receiver external clock timing and Table 81 lists the timing parameters for the receiver timing with the external clock.

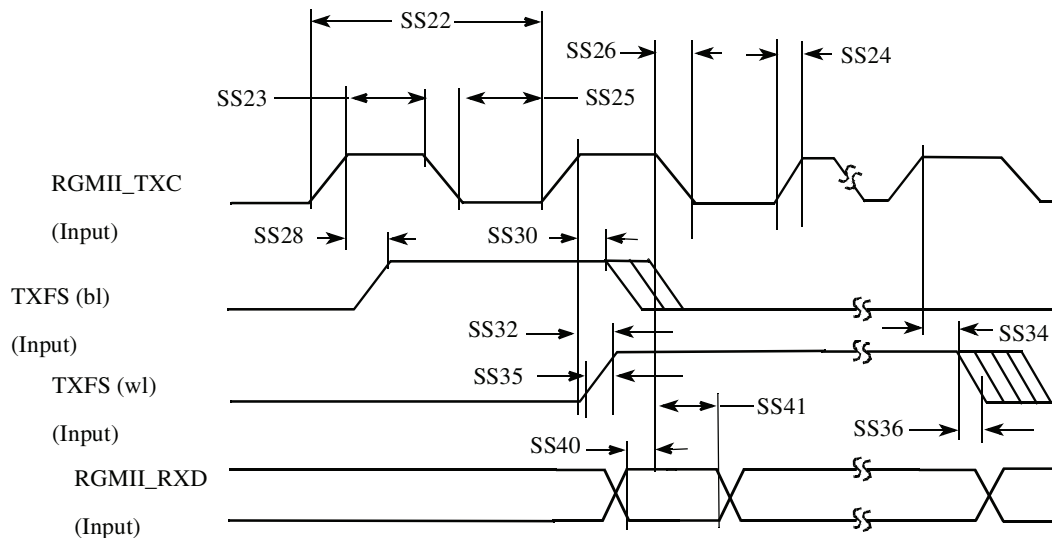


Figure 94. SSI Receiver External Clock Timing Diagram

Table 81. SSI Receiver Timing with External Clock

ID	Parameter	Min	Max	Unit
External Clock Operation				
SS22	(Tx/Rx) CK clock period	81.4	—	ns
SS23	(Tx/Rx) CK clock high period	36	—	ns
SS24	(Tx/Rx) CK clock rise time	—	6.0	ns
SS25	(Tx/Rx) CK clock low period	36	—	ns
SS26	(Tx/Rx) CK clock fall time	—	6.0	ns
SS28	(Rx) CK high to FS (bl) high	-10	15.0	ns
SS30	(Rx) CK high to FS (bl) low	10	—	ns
SS32	(Rx) CK high to FS (wl) high	-10	15.0	ns
SS34	(Rx) CK high to FS (wl) low	10	—	ns
SS35	(Tx/Rx) External FS rise time	—	6.0	ns
SS36	(Tx/Rx) External FS fall time	—	6.0	ns
SS40	SRXD setup time before (Rx) CK low	10	—	ns
SS41	SRXD hold time after (Rx) CK low	2	—	ns

## 6.1.2 21 x 21 mm Supplies Contact Assignments and Functional Contact Assignments

Table 91 shows supplies contact assignments for the 21 x 21 mm package.

**Table 91. 21 x 21 mm Supplies Contact Assignments**

Supply Rail Name	Ball(s) Position(s)	Remark
CSI_REXT	D4	
DRAM_VREF	AC2	
DSI_REXT	G4	
GND	A4, A8, A13, A25, B4, C1, C4, C6, C10, D3, D6, D8, E5, E6, E7, F5, F6, F7, F8, G3, G10, G19, H8, H12, H15, H18, J2, J8, J12, J15, J18, K8, K10, K12, K15, K18, L2, L5, L8, L10, L12, L15, L18, M8, M10, M12, M15, M18, N8, N10, N15, N18, P8, P10, P12, P15, P18, R8, R12, R15, R17, T8, T11, T12, T15, T17, T19, U8, U11, U12, U15, U17, U19, V8, V19, W3, W7, W8, W9, W10, W11, W12, W13, W15, W16, W17, W18, W19, Y5, Y24, AA7, AA10, AA13, AA16, AA19, AA22, AB3, AB24, AD4, AD7, AD10, AD13, AD16, AD19, AD22, AE1, AE25	
HDMI_REF	J1	
HDMI_VP	L7	
HDMI_VPH	M7	
NVCC_CSI	N7	Supply of the camera sensor interface
NVCC_DRAM	R18, T18, U18, V9, V10, V11, V12, V13, V14, V15, V16, V17, V18	Supply of the DDR interface
NVCC_EIM	K19, L19, M19	Supply of the EIM interface
NVCC_ENET	R19	Supply of the ENET interface
NVCC_GPIO	P7	Supply of the GPIO interface
NVCC_JTAG	J7	Supply of the JTAG tap controller interface
NVCC_LCD	P19	Supply of the LCD interface
NVCC_LVDS2P5	V7	Supply of the LVDS display interface and DDR pre-drivers
NVCC_MIPI	K7	Supply of the MIPI interface
NVCC_NANDF	G15	Supply of the raw NAND Flash memories interface
NVCC_PLL_OUT	E8	
NVCC_RGMII	G18	Supply of the ENET interface
NVCC_SD1	G16	Supply of the SD card interface
NVCC_SD2	G17	Supply of the SD card interface
NVCC_SD3	G14	Supply of the SD card interface